FMB3030CG

N And P-Channel Enhancement Mode Power MOSFET

N-Channel

VDS = 30V,ID =30A

$R_{DS(ON)}$ < 8.5mΩ @ VGS=10V

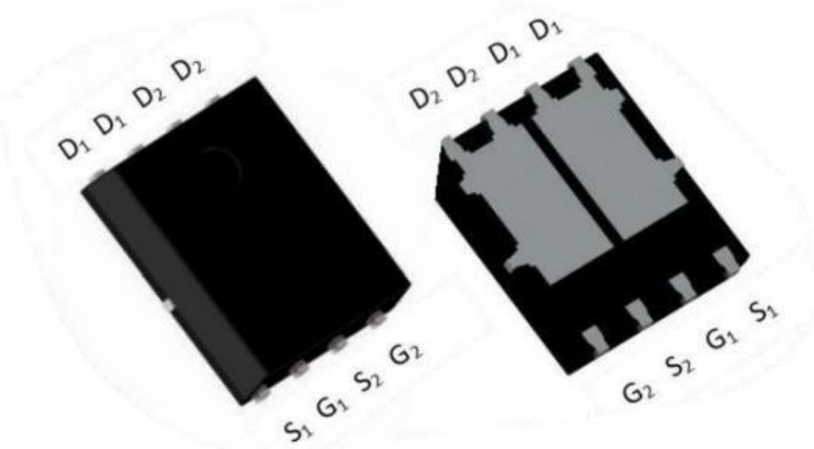
$R_{DS(ON)}$ <11.5mΩ @ VGS=4.5V

P-Channel

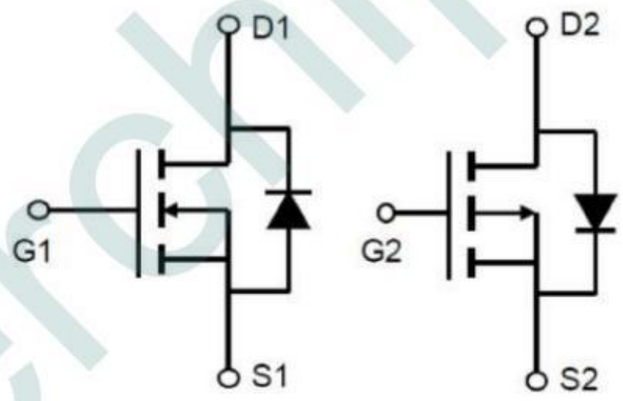
VDS = -30V,ID = -30A

$R_{DS(ON)}$ < 14mΩ @ VGS=-10V

$R_{DS(ON)}$ < 19.5mΩ @ VGS=-4.5V



PDFN-8 5*6



Schematic diagram

Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter		Value		Units
			N	P	
V_{DSS}	Drain-Source Voltage		30	-30	V
V_{GSS}	Gate-Source Voltage		±20	±20	V
I_D	Continuous Drain Current	T_C = 25℃	30	-30	A
		T_C = 100℃	22	-20	A
I_{DM}	Pulsed Drain Current note1		106	-93	A
E_{AS},E_{AR}	Single Pulsed Avalanche Energy note2		90	182	mJ
P_D	Power Dissipation	T_C = 25℃	15	17	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		8.3	7.2	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	-55 to +150	℃

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